

3N153  
T-31-25

## Silicon Insulated-Gate Field-Effect Transistor

For Chopper and Multiplex Service in Communications,  
Navigation, and Instrumentation Equipment and in  
Industrial Control Circuits

### Features:

- Excellent thermal stability
- Virtually zero inherent offset voltage
- Low leakage current: 50 pA max.
- Low "on" resistance— $r_{DS(on)} = 200\Omega$  typ.
- High "off" resistance— $R_{DS(off)} = 10^{10}\Omega$  typ.
- Low feedback capacitance— $C_{rs} = 0.34$  pF typ.
- Low input capacitance— $C_{is} = 6$  pF typ.

### Applications:

- Choppers
- Multiplexers
- Servo Amplifiers
- Computer Operational Amplifiers
- Sampling Circuits
- Electrometer Amplifiers

RCA 3N153\* is a silicon, insulated-gate field-effect transistor of the N-channel depletion type, utilizing the MOS\* construction. It is intended primarily for critical chopper and multiplex applications up to 60 MHz.

The insulated gate provides a very high value of input resistance ( $10^{10}$  ohms typ.) which is relatively insensitive to temperature and is independent of gate-bias conditions (positive, negative, or zero bias). The 3N153 also features extremely low feedback capacitance (0.34pF typ.) and virtually zero inherent offset voltage.

This transistor features a Terminal Arrangement in which the gate and source connections are interchanged to provide maximum isolation between the output (drain) and the input (gate)

terminals. Although this new basing configuration does not appreciably change the measured device feedback capacitance, it permits the use of external inter-terminal shields to reduce the feedback due to external capacitances, particularly on printed circuit boards. This feature makes it possible to minimize feedthrough capacitance.

The 3N153 is hermetically sealed in the JEDEC TO-72 package and features a gate metallization that covers the entire source-to-drain channel.

- Formerly Dev. No. TA7352.
- Metal-Oxide-Semiconductor.

### Maximum Ratings, Absolute-Maximum Values:

(Substrate connected to source unless otherwise specified)

DRAIN-TO-SOURCE VOLTAGE, $V_{DS}$	..... +20 max. V
DRAIN-TO-SUBSTRATE VOLTAGE, $V_{DE}$	..... +20, -0.3 max. V
SOURCE-TO-SUBSTRATE VOLTAGE, $V_{SE}$	..... +20, -0.3 max. V
DC GATE-TO-SOURCE VOLTAGE, $V_{GS}$	..... +6, -8 max. V
PEAK GATE-TO-SOURCE VOLTAGE, $V_{GS}$	..... $\pm 14$ max. V
DRAIN CURRENT, $I_D$ (Pulse duration 20 ms, duty factor $\leq 0.10$ )	..... 50 max. mA

### TRANSISTOR DISSIPATION, $P_T$ :

At ambient temperatures	..... 400 max. mW
from -65 to +25°C	..... derate linearly at 2.67 mW/°C
above 25°C	.....

### AMBIENT TEMPERATURE RANGE:

Storage	..... -65 to +175°C
Operating	..... -65 to +175°C

### LEAD TEMPERATURE

(During soldering):	..... 265 max. °C
At distance $\geq 1/32$ " to seating surface for 10 seconds max.	.....



## Small-Signal MOSFETs

## 3N153

ELECTRICAL CHARACTERISTICS, at  $T_A = 25^\circ\text{C}$ , Unless Otherwise Specified. Substrate Connected to Source.

CHARACTERISTICS	SYMBOLS	TEST CONDITIONS	LIMITS Type 3N153			UNITS
			Min.	Typ.	Max.	
Gate-Leakage Current	$I_{GSS}$	$V_{GS} = +6, -8\text{V}; V_{DS} = 0\text{V}; T_A = 25^\circ\text{C}$ $V_{GS} = +6, -8\text{V}; V_{DS} = 0\text{V}; T_A = 125^\circ\text{C}$	-	0.1	50 1	pA nA
Static Drain-to-Source "ON" Resistance	$r_{DS(on)}$	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}$	-	200	300	$\Omega$
Drain-to-Source "OFF" Resistance	$R_{DS(off)}$	$V_{GS} = -8\text{V}, V_{DS} = +1\text{V}$	$10^9$	$10^{10}$	-	$\Omega$
Drain-to-Source Cutoff Current	$I_{D(off)}$	$V_{GS} = -8\text{V}, V_{DS} = +1\text{V}, T_A = 25^\circ\text{C}$ $V_{GS} = -8\text{V}, V_{DS} = +1\text{V}, T_A = 125^\circ\text{C}$	-	0.1 0.1	1 1	nA $\mu\text{A}$
Small-Signal, Short-Circuit, Reverse Transfer Capacitance	$C_{rss}$	$V_{GS} = -8\text{V}, V_{DS} = 0\text{V}, f = 1\text{ MHz}$ $V_{DS} = 15\text{V}, I_D = 5\text{ mA}, f = 1\text{ MHz}$	-	0.34 0.12	0.5 0.2	pF pF
Small-Signal, Short-Circuit, Input Capacitance	$C_{iss}$	$V_{GS} = -8\text{V}, V_{DS} = 0\text{V}, f = 1\text{ MHz}$	-	6	8	pF
Small-Signal, Drain-to-Source Capacitance	$C_{ds}$	$V_{DS} = 0\text{V}, V_{GS} = -8\text{V}, f = 1\text{ MHz}$	-	-	3	pF
Zero-Gate-Bias Forward Transconductance	$g_{fs}$	$V_{GS} = 0\text{V}, V_{DS} = +15\text{V}$	-	10,000	-	$\mu\text{mho}$
Offset Voltage	$V_0$	$V_{GS} = +6, -8\text{V}; V_{DS} = 0\text{V}$	-	0*	-	V

\* In measurements of Offset Voltage, thermocouple effects and contact potentials in the measurement setup may cause erroneous readings of 1 microvolt or more. These errors may be minimized by the use of solder having a low thermal e.m.f., such as Leeds & Northrup No.107-1.0.1, or equivalent.

## OPERATING CONSIDERATIONS

The flexible leads of the 3N153 are usually soldered to the circuit elements. As in the case of any high-frequency semiconductor device, the tips of soldering irons should be grounded, and appropriate precautions should be taken to protect the device against high electric fields.

This device should not be connected into or disconnected from circuits with the power on because high transient voltages may cause permanent damage to the device.

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## TYPICAL CHARACTERISTICS

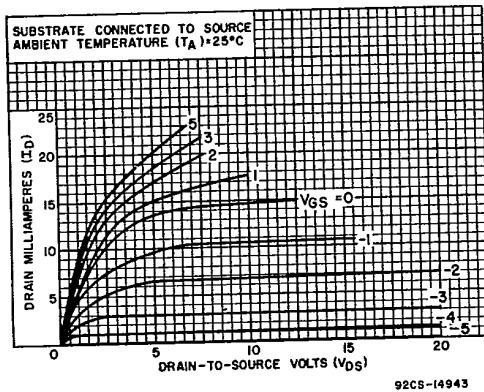


Fig. 1 - Drain current vs. drain-to-source voltage.

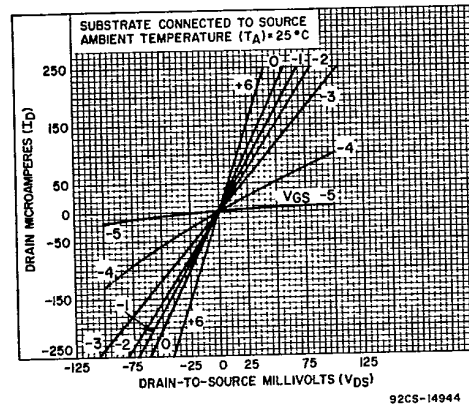


Fig. 2 - Low-level drain current vs. drain-to-source voltage.

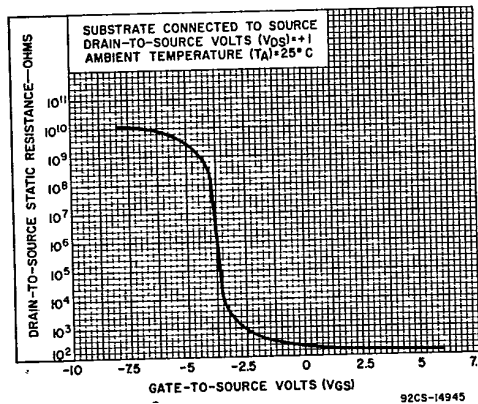
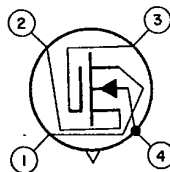


Fig. 3 - Drain-to-source static resistance vs. gate-to-source voltage.

## TERMINAL DIAGRAM



- 1 - Drain
- 2 - Source
- 3 - Insulated Gate
- 4 - Bulk (Substrate) and Case